

Demonstration of Irradiation-resistant 4H-SiC Based Photoelectrochemical Water Splitting

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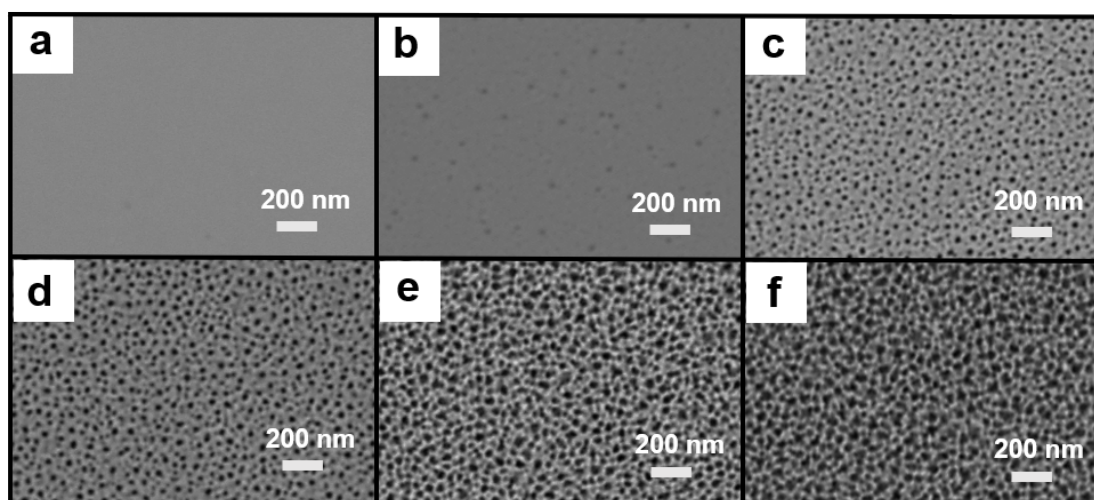


Figure S1: SEM images of samples etched for different durations at 3 V (a) Original 4H-SiC, (b) 2 min, (c) 5 min, (d) 10 min, (e) 20 min and (f) 30 min.

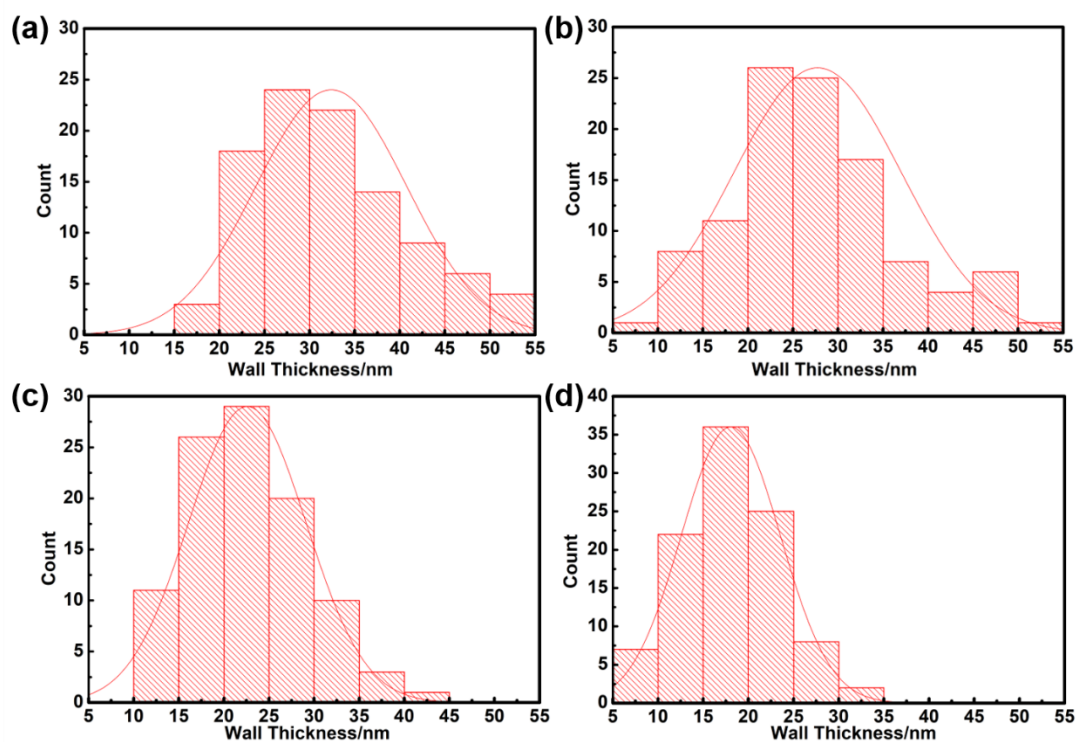


Figure S2: Statistical chart of pore wall thickness of nanoporous arrays photoanodes.

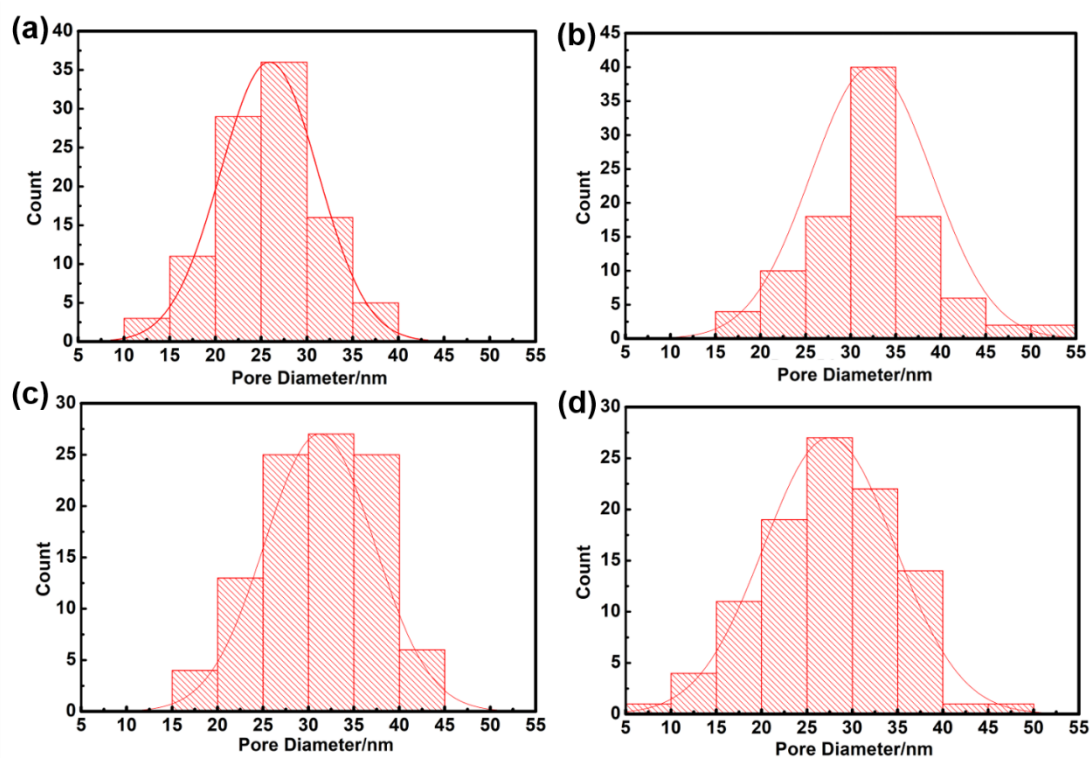


Figure S3: Statistical chart of pore diameter of nanoporous arrays photoanodes.